Features

- Fast read access time – 45ns
- Low-power CMOS operation
  - 100µA max standby
  - 20mA max active at 5MHz
- JEDEC standard packages
  - 28-lead PDIP
  - 32-lead PLCC
- 5V ± 10% supply
- High-reliability CMOS technology
  - 2,000V ESD protection
  - 200mA latchup immunity
- Rapid programming algorithm – 100µs/byte (typical)
- CMOS- and TTL-compatible inputs and outputs
- Integrated product identification code
- Industrial and automotive temperature ranges
- Green (Pb/halide-free) packaging option

512K (64K x 8) One-time Programmable, Read-only Memory

Atmel AT27C512R

1. Description

The Atmel® AT27C512R is a low-power, high-performance, 524,288-bit, one-time programmable, read-only memory (OTP EPROM) organized as 64K by 8 bits. It requires only one 5V power supply in normal read mode operation. Any byte can be accessed in less than 45ns, eliminating the need for speed reducing WAIT states on high-performance microprocessor systems.

The Atmel scaled CMOS technology provides high speed, lower active power consumption, and significantly faster programming. Power consumption is typically only 8mA in active mode and less than 10µA in standby mode.

The AT27C512R is available in a choice of industry-standard, JEDEC-approved, one-time programmable (OTP) PDIP and PLCC packages. All devices feature two-line control ($\overline{CE}$, $\overline{OE}$) to give designers the flexibility to prevent bus contention.

With 64K byte storage capability, the AT27C512R allows firmware to be stored reliably and to be accessed by the system without the delays of mass storage media.

The AT27C512R has additional features to ensure high quality and efficient production use. The rapid programming algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100µs/byte. The integrated product identification code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages.

2. Pin configurations

Pin name	Function
A0 – A15	Addresses
O0 – O7	Outputs
$\overline{CE}$	Chip enable
$\overline{OE}$/VPP	Output enable/ Program supply
NC	No connect

32-lead PLCC
Top view

```
          A7 A12 A15 NC VCC A14 A13
           4   3   2   1  32  31  30
A6  5                              29  A8
A5  6                              28  A9
A4  7                              27  A11
A3  8                              26  NC
A2  9                              25  OE/VPP
A1  10                             24  A10
A0  11                             23  CE
NC  12                             22  O7
O0  13                             21  O6
          14  15  16  17  18  19  20
          O1  O2 GND  NC  O3  O4  O5
```

28-lead PDIP
Top view

```
A15  1          28  VCC
A12  2          27  A14
 A7  3          26  A13
 A6  4          25  A8
 A5  5          24  A9
 A4  6          23  A11
 A3  7          22  OE/VPP
 A2  8          21  A10
 A1  9          20  CE
 A0 10          19  O7
 O0 11          18  O6
 O1 12          17  O5
 O2 13          16  O4
GND 14          15  O3
```

Note: PLCC package pins 1 and 17
         are don't connect

3. System considerations

Switching between active and standby conditions via the chip enable pin may produce transient voltage excursions. Unless accommodated by the system design, these transients may exceed datasheet limits, resulting in device nonconformance. At a minimum, a 0.1µF, high-frequency, low inherent inductance, ceramic capacitor should be utilized for each device. This capacitor should be connected between the V_{CC} and ground terminals of the device, as close to the device as possible. Additionally, to stabilize the supply voltage level on printed circuit boards with large EPROM arrays, a 4.7µF bulk electrolytic capacitor should be utilized, again connected between the V_{CC} and ground terminals. This capacitor should be positioned as close as possible to the point where the power supply is connected to the array.

Figure 3-1.   Block diagram
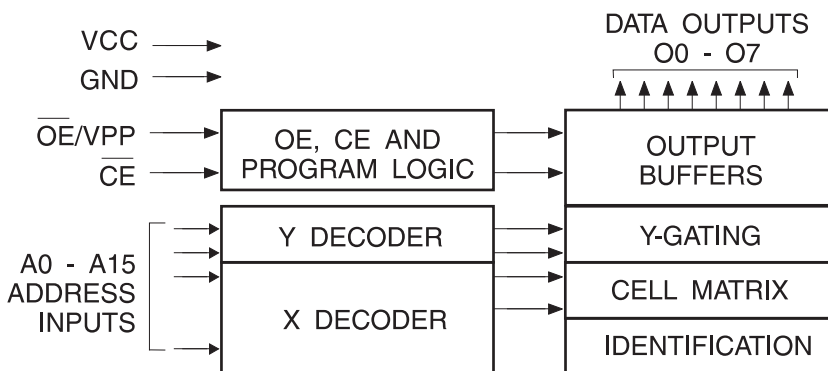
4. Absolute maximum ratings*

Temperature under bias . . . . -55°C to + 125°C

Storage temperature . . . . -65°C to + 150°C

Voltage on any pin with
respect to ground . . . . -2.0V to + 7.0V[1]

Voltage on A9 with
respect to ground . . . . -2.0V to + 14.0V[1]

V_{PP} supply voltage with
respect to ground . . . . -2.0V to + 14.0V[1]

*NOTICE: Stresses beyond those listed under "Absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: 1.   Minimum voltage is –0.6V DC, which may undershoot to –2.0V for pulses of less than 20ns. Maximum output pin voltage is V_{CC} + 0.75V DC, which may overshoot to +7.0V for pulses of less than 20ns.

5. DC and AC characteristics

Table 5-1.   Operating modes

Mode/Pin	$\overline{CE}$	$\overline{OE}/V_{PP}$	Ai	Outputs
Read	V_{IL}	V_{IL}	Ai	D_{OUT}
Output disable	V_{IL}	V_{IH}	X[1]	High Z
Standby	V_{IH}	X[1]	X	High Z
Rapid program[2]	V_{IL}	V_{PP}	Ai	D_{IN}
PGM inhibit	V_{IH}	V_{PP}	X[1]	High Z
Product identification[4]	V_{IL}	V_{IL}	A9 =V_H[3] A0 = V_{IH} or V_{IL} A1 - A15 = V_{IL}	Identification code

Notes: 1.   X can be V_{IL} or V_{IH}.
2.   Refer to programming characteristics.
3. V_H = 12.0 ± 0.5V.
4.   Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9, which is set to V_H, and A0, which is toggled low (V_{IL}) to select the manufacturer's identification byte and high (V_{IH}) to select the device code byte.

Table 5-2.   DC and AC operating conditions for read operation

		Atmel AT27C512R	
		-45	-70
Operating temp. (case)	Ind.	–40°C - 85°C	–40°C - 85°C
	Auto.		–40°C - 125°C
V_{CC} supply		5V ± 10%	5V ± 10%

Table 5-3. DC and operating characteristics for read operation

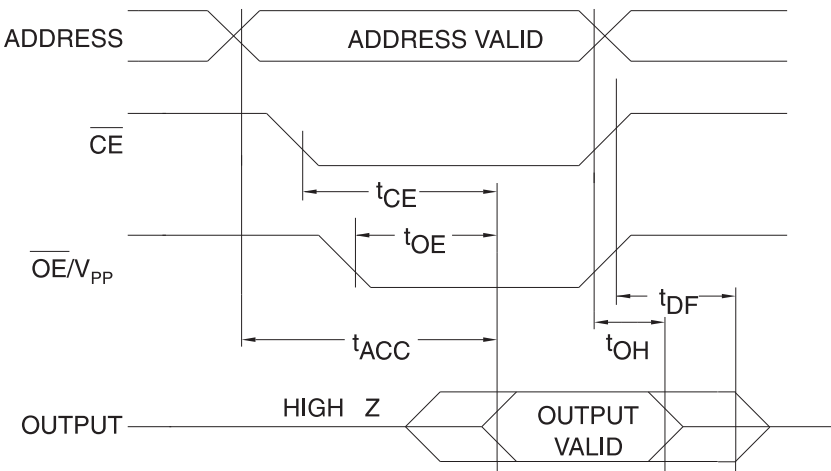| Symbol	Parameter	Condition		Min	Max	Units
I_{LI}	Input load current	V_{IN} = 0V to V_{CC}	Ind.		±1	µA
			Auto.		±5	µA
I_{LO}	Output leakage current	V_{OUT} = 0V to V_{CC}	Ind.		±5	µA
			Auto.		±10	µA
I_{SB}	V_{CC}[1] standby current	I_{SB1} (CMOS), $\overline{CE}$ = $V_{CC \pm}$ 0.3V			100	µA
		I_{SB2} (TTL), $\overline{CE}$ = 2.0 to $V_{CC +}$ 0.5V			1	mA
I_{CC}	V_{CC} active current	f = 5MHz, I_{OUT} = 0mA, $\overline{CE}$ = V_{IL}			20	mA
V_{IL}	Input low voltage			-0.6	0.8	V
V_{IH}	Input high voltage			2.0	V_{CC} + 0.5	V
V_{OL}	Output low voltage	I_{OL} = 2.1mA			0.4	V
V_{OH}	Output high voltage	I_{OH} = -400µA		2.4		V

Note: 1. V_{CC} must be applied simultaneously with or before $\overline{OE}/V_{PP}$, and removed simultaneously with or after $\overline{OE}/V_{PP}$.

Table 5-4. AC characteristics for read operation

Symbol	Parameter	Condition	Atmel AT27C512R				Units
			-45		-70		
			Min	Max	Min	Max	
t_{ACC}[1]	Address to output delay	$\overline{CE}$ = $\overline{OE}/V_{PP}$ = V_{IL}		45		70	ns
t_{CE}[1]	$\overline{CE}$ to output delay	$\overline{OE}/V_{PP}$ = V_{IL}		45		70	ns
t_{OE}[1]	$\overline{OE}/V_{PP}$ to output delay	$\overline{CE}$ = V_{IL}		20		30	ns
t_{DF}[1]	$\overline{OE}/V_{PP}$ or $\overline{CE}$ high to output float, whichever occurred first			20		25	ns
t_{OH}	Output hold from address, $\overline{CE}$ or $\overline{OE}/V_{PP}$, whichever occurred first		7		7		ns

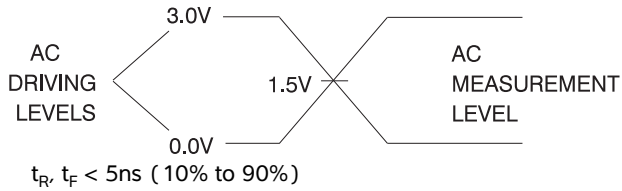Note: 1. See AC waveforms for read operation.

Figure 5-1.   AC waveforms for read operation[1]

ADDRESS   ADDRESS VALID

$\overline{CE}$

t_{CE}

t_{OE}

$\overline{OE}/V_{PP}$

t_{DF}

t_{ACC} t_{OH}

OUTPUT ——— HIGH Z   OUTPUT
VALID

Notes: 1.   Timing measurement reference level is 1.5V for –45 devices. Input AC drive levels are V_{IL} = 0.0V and V_{IH} = 3.0V. Timing measurement reference levels for all other speed grades are V_{OL} = 0.8V and V_{OH} = 2.0V. Input AC drive levels are V_{IL} = 0.45V and V_{IH} = 2.4V.

2. $\overline{OE}/V_{PP}$ may be delayed up to t_{CE} – t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}.

3. $\overline{OE}/V_{PP}$ may be delayed up to t_{ACC} – t_{OE} after the address is valid without impact on t_{ACC}.

4.   This parameter is only sampled, and is not 100% tested.

5.   Output float is defined as the point when data is no longer driven.

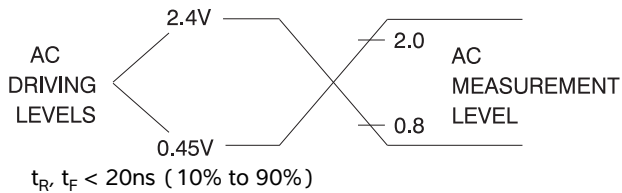Figure 5-2.   Input test waveforms and measurement levels

For –45 devices only:

3.0V

AC
DRIVING   1.5V   AC
LEVELS   MEASUREMENT
LEVEL

0.0V

t_R, t_F < 5ns (10% to 90%)

For –70 devices:

2.4V

AC   2.0
DRIVING   AC
LEVELS   MEASUREMENT
LEVEL
0.8

0.45V

t_R, t_F < 20ns (10% to 90%)

Figure 5-3.   Output test load

1.3V

(1N914)

3.3K

OUTPUT
PIN

CL

Note: 1. C_L = 100pF including jig capacitance, except for the -45 devices, where C_L = 30pF.

Table 5-5. Pin capacitance

f = 1MHz, T = 25°C[1]

Symbol	Typ	Max	Units	Conditions
C_{IN}	4	6	pF	V_{IN} = 0V
C_{OUT}	8	12	pF	V_{OUT} = 0V

Note: 1. Typical values for nominal supply voltage. This parameter is only sampled, and is not 100% tested.

Figure 5-4. Programming Waveforms[1]

Notes: 1. The input timing reference is 0.8V for V_{IL} and 2.0V for V_{IH}.

2. t_{OE} and t_{DFP} are characteristics of the device, but must be accommodated by the programmer.

Table 5-6.   DC programming characteristics

$T_A = 25 \pm 5°C$, $V_{CC} = 6.5 \pm 0.25V$, $\overline{OE}/V_{PP} = 13.0 \pm 0.25V$

Symbol	Parameter	Test conditions	Limits		Units
			Min	Max	
I_{LI}	Input load current	$V_{IN} = V_{IL}, V_{IH}$		±10	µA
V_{IL}	Input low level		-0.6	0.8	V
V_{IH}	Input high level		2.0	$V_{CC} + 1$	V
V_{OL}	Output low voltage	$I_{OL} = 2.1mA$		0.4	V
V_{OH}	Output high voltage	$I_{OH} = -400µA$	2.4		V
I_{CC2}	V_{CC} supply current (program and verify)			25	mA
I_{PP2}	$\overline{OE}/V_{PP}$ current	$\overline{CE} = V_{IL}$		25	mA
V_{ID}	A9 product identification voltage		11.5	12.5	V

Table 5-7.   AC programming characteristics

$T_A = 25 \pm 5°C$, $V_{CC} = 6.5 \pm 0.25V$, $\overline{OE}/V_{PP} = 13.0 \pm 0.25V$

Symbol	Parameter	Test conditions[1]	Limits		Units
			Min	Max	
t_{AS}	Address setup time	Input rise and fall times (10% to 90%) 20ns Input pulse levels 0.45V to 2.4V Input timing reference level 0.8V to 2.0V Output timing reference level 0.8V to 2.0V	2		µs
t_{OES}	$\overline{OE}/V_{PP}$ setup time		2		µs
t_{OEH}	$\overline{OE}/V_{PP}$ hold time		2		µs
t_{DS}	Data setup time		2		µs
t_{AH}	Address hold time		0		µs
t_{DH}	Data hold time		2		µs
t_{DFP}	$\overline{CE}$ high to output float delay[2]		0	130	ns
t_{VCS}	V_{CC} setup time		2		µs
t_{PW}	$\overline{CE}$ program pulse width[3]		95	105	µs
t_{DV}	Data valid from $\overline{CE}$[2]			1	µs
t_{VR}	$\overline{OE}/V_{PP}$ recovery time		2		µs
t_{PRT}	$\overline{OE}/V_{PP}$ pulse rise time during programming		50		ns

Notes: 1. V_{CC} must be applied simultaneously with or before $\overline{OE}/V_{PP}$ and removed simultaneously with or after $\overline{OE}/V_{PP}$.

2. This parameter is only sampled, and is not 100% tested. Output float is defined as the point where data is no longer driven. See timing diagram.

3. Program pulse width tolerance is 100µsec ± 5%.

Table 5-8.   The Atmel AT27C512R integrated product identification code

Codes	Pins									Hex data
	A0	O7	O6	O5	O4	O3	O2	O1	O0	
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device type	1	0	0	0	0	1	1	0	1	0D

6. Rapid programming algorithm

A 100µs $\overline{CE}$ pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5V and $\overline{OE}/V_{PP}$ is raised to 13.0V. Each address is first programmed with one 100µs $\overline{CE}$ pulse without verification. Then a verification/reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100µs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. $\overline{OE}/V_{PP}$ is then lowered to V_{IL} and V_{CC} to 5.0V. All bytes are read again and compared with the original data to determine if the device passes or fails.

Figure 6-1.   Rapid programming algorithm
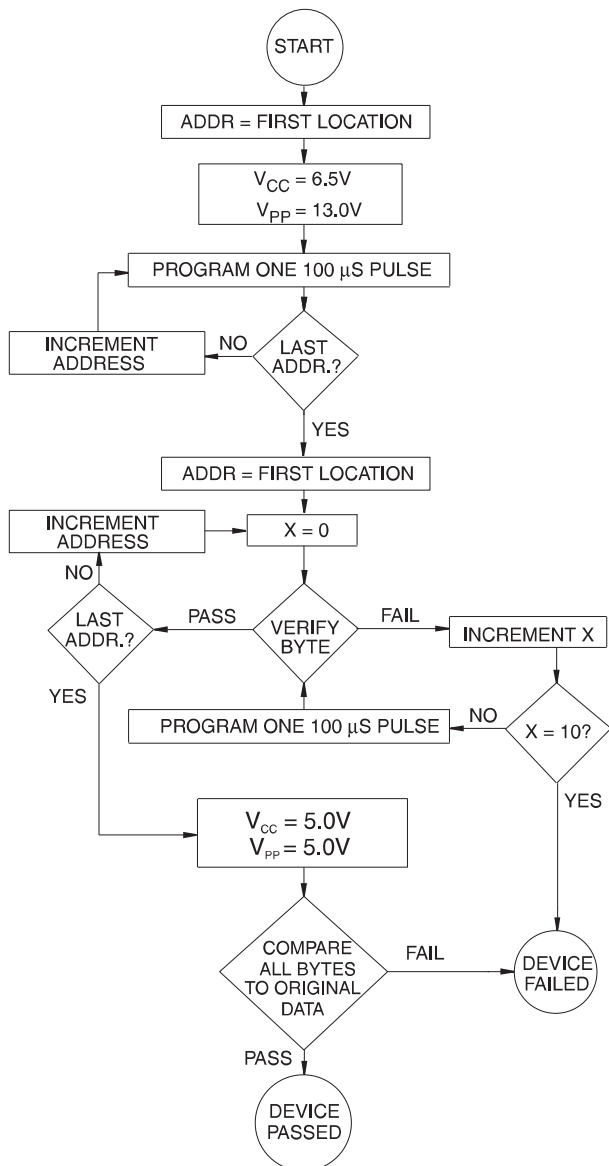
7.   Ordering information

Green package (Pb/halide-free)

t_{ACC} (ns)	I_{CC} (mA)		Atmel ordering code	Package	Lead finish	Operation range
	Active	Standby				
45	20	0.1	AT27C512R-45JU AT27C512R-45PU	32J 28P6	Matte tin Matte tin	Industrial (-40°C to 85°C)
70	20	0.1	AT27C512R-70JU AT27C512R-70PU	32J 28P6	Matte tin Matte tin	Industrial (-40°C to 85°C)

Package type	
32J	32-lead, plastic, J-leaded chip carrier (PLCC)
28P6	28-lead, 0.600" wide, plastic, dual inline package (PDIP)

8. Packaging information

32J – PLCC

Notes: 1. This package conforms to JEDEC reference MS-016, variation AE.
2. Dimensions D1 and E1 do not include mold protrusion.
   Allowable protrusion is .010" (0.254mm) per side. Dimension D1
   and E1 include mold mismatch and are measured at the extreme
   material condition at the upper or lower parting line.
3. Lead coplanarity is 0.004" (0.10mm) maximum.

COMMON DIMENSIONS
(Unit of measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	3.175	–	3.556	
A1	1.524	–	2.413	
A2	0.381	–	–	
D	12.319	–	12.573	
D1	11.354	–	11.506	Note 2
D2	9.906	–	10.922	
E	14.859	–	15.113	
E1	13.894	–	14.046	Note 2
E2	12.471	–	13.487	
B	0.660	–	0.813	
B1	0.330	–	0.533	
e	1.270 TYP			

10/04/01

	TITLE	DRAWING NO.	REV.
Package drawing contact: packagedrawings@atmel.com	32J, 32-lead, plastic J-leaded chip carrier (PLCC)	32J	B

28P6 – PDIP

Notes: 1. This package conforms to JEDEC reference MS-011, variation AB
2. Dimensions D and E1 do not include mold flash or protrusion
   mold flash or protrusion shall not exceed 0.25mm (0.010")

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	–	–	4.826	
A1	0.381	–	–	
D	36.703	–	37.338	Note 2
E	15.240	–	15.875	
E1	13.462	–	13.970	Note 2
B	0.356	–	0.559	
B1	1.041	–	1.651	
L	3.048	–	3.556	
C	0.203	–	0.381	
eB	15.494	–	17.526	
e	2.540 TYP			

09/28/01

	TITLE	DRAWING NO.	REV.
Package drawing contact: packagedrawings@atmel.com	28P6, 28-lead (0.600"/15.24mm wide) plastic dual inline package (PDIP)	28P6	B

9. Revision history

Doc. rev.	Date	Comments
0015Q	10/2011	Correct pinout note
0015P	04/2011	Remove TSOP and SOIC packages Add lead finish to ordering information
0015O	12/2007	

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